

Title (en)
Removal of substrate perimeter material.

Title (de)
Entfernen von Material vom Rand eines Substrates.

Title (fr)
Enlèvement de matériau du pourtour d'un substrat.

Publication
EP 0529888 A1 19930303 (EN)

Application
EP 92307432 A 19920813

Priority
US 74837691 A 19910822

Abstract (en)
Perimeter material is removed from substrates by stacking the substrates and subjecting them to a plasma etch. In an exemplary application, the perimeter (42) of a silicon wafer dielectric cap (41) (typically silicon nitride) is removed by stacking the wafers (31, 32...) in intimate contact, and etching the wafers in a barrel etcher. A well-controlled removal of the cap perimeter is obtained, allowing for a smooth epitaxial deposition at the wafer edge in a subsequent operation. An additional benefit is smoothing of the substrate edge contour, which reduces scratching of wafer cassettes and other handling equipment. <IMAGE>

IPC 1-7
H01L 21/302; **H01L 21/306**; **H01L 21/311**

IPC 8 full level
H01L 21/304 (2006.01); **H01L 21/20** (2006.01); **H01L 21/311** (2006.01)

CPC (source: EP US)
H01L 21/31116 (2013.01 - EP US); **Y10S 438/928** (2013.01 - EP US)

Citation (search report)

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